

Matthew J Davies

List of Publications by Year in descending order

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Version: 2024-02-01

8
papers

58
citations

1874746
5
h-index

1762888
8
g-index

8
all docs

8
docs citations

8
times ranked

151
citing authors

#	ARTICLE	IF	CITATIONS
1	Room temperature PL efficiency of InGaN/GaN quantum well structures with prelayers as a function of number of quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 248-251.	0.8	7
2	A study of the optical and polarisation properties of InGaN/GaN multiple quantum wells grown on a-plane and m-plane GaN substrates. <i>Science and Technology of Advanced Materials</i> , 2016, 17, 736-743.	2.8	5
3	A study of the inclusion of prelayers in InGaN/GaN single- and multiple-quantum-well structures. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 866-872.	0.7	16
4	Carrier distributions in InGaN/GaN light-emitting diodes. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 890-894.	0.7	6
5	Dynamics of carrier redistribution processes in InGaN/GaN quantum well structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 738-741.	0.8	2
6	Effects of an InGaN prelayer on the properties of InGaN/GaN quantum well structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 710-713.	0.8	10
7	High excitation density recombination dynamics in InGaN/GaN quantum well structures in the droop regime. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 694-697.	0.8	2
8	The effects of varying threading dislocation density on the optical properties of InGaN/GaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 750-753.	0.8	10